

STARPOWER

SEMICONDUCTOR™

IGBT

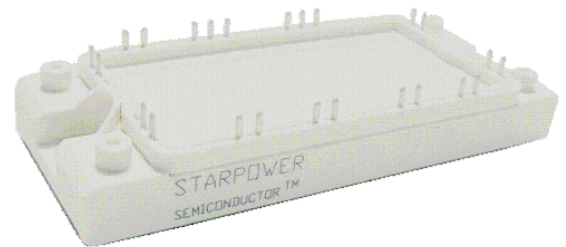
GD50HHU60C5S

Molding Type Module

600V/50A 4 in one-package

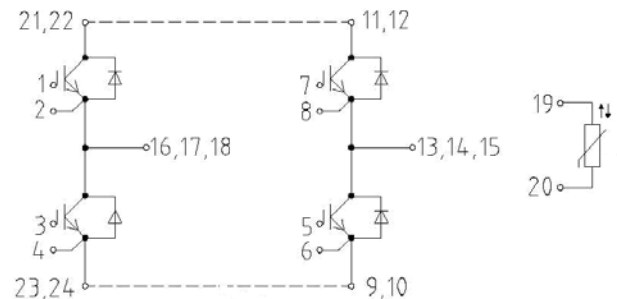
General Description

STARPOWER IGBT Power Module provides ultrafast switching speed as well as short circuit ruggedness. It's designed for the applications such as electronic welder and Inductive heating.



Features

- High short circuit capability, self limiting to $6 \cdot I_{Cnom}$
- 10us short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Rugged with ultrafast performance
- Square RBSOA
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DCB technology



Equivalent Circuit Schematic

Typical Applications

- Switching mode power supplies at $f_{sw} > 30\text{kHz}$
- Inductive heating
- UPS
- Electronic welder at $f_{sw} > 30\text{kHz}$

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Description	GD50HHU60C5S	Units
V_{CES}	Collector-Emitter Voltage	600	V
V_{GES}	Gate-Emitter Voltage	$\pm 20\text{V}$	V
I_C	Collector Current @ $T_C=25^\circ\text{C}$, $T_J=150^\circ\text{C}$	75	A
	@ $T_C=80^\circ\text{C}$, $T_J=150^\circ\text{C}$	50	
$I_{CM(1)}$	Pulsed Collector Current @ $T_C=80^\circ\text{C}$	100	A
I_F	Diode Continuous Forward Current	50	A
I_{FM}	Diode Maximum Forward Current	100	A
P_D	Maximum power Dissipation @ $T_J=150^\circ\text{C}$	230	W
T_{SC}	Short Circuit Withstand Time @ $T_J=125^\circ\text{C}$	10	μs
T_J	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-40 to +150	$^\circ\text{C}$
I^2t -value, Diode	$V_R=0\text{V}$, $t=10\text{ms}$, $T_J=125^\circ\text{C}$	400	A^2s
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	2500	V
Mounting Torque	Mounting Screw:M5	3 to 6	N.m

Notes:

(1) Repetitive rating: Pulse width limited by max. junction temperature

Electrical Characteristics of IGBT $T_C=25^\circ\text{C}$ unless otherwise noted**Off Characteristics**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{CES}	Collector-Emitter Breakdown Voltage	$T_J=25^\circ\text{C}$	600			V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}$, $V_{GE}=0\text{V}$, $T_J=25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}$, $V_{CE}=0\text{V}$, $T_J=25^\circ\text{C}$			100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=250\mu\text{A}$, $V_{CE}=V_{GE}$, $T_J=25^\circ\text{C}$	3.5	4.5	5.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=50\text{A}$, $V_{GE}=15\text{V}$, $T_J=25^\circ\text{C}$		2.5	2.9	V
		$I_C=50\text{A}$, $V_{GE}=15\text{V}$, $T_J=125^\circ\text{C}$		2.7	3.1	

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300V, I_C=50A,$ $R_G=10\Omega, V_{GE} = \pm 15V,$ $T_j=25^\circ C$		46		ns
t_r	Rise Time			28		ns
$t_{d(off)}$	Turn-Off Delay Time			185		ns
t_f	Fall Time			31		ns
E_{on}	Turn-On Switching Loss			1.5		mJ
E_{off}	Turn-Off Switching Loss			3.3		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300V, I_C=50A,$ $R_G=10\Omega, V_{GE} = \pm 15V,$ $T_j=125^\circ C$		55		ns
t_r	Rise Time			40		ns
$t_{d(off)}$	Turn-Off Delay Time			215		ns
t_f	Fall Time			42		ns
E_{on}	Turn-On Switching Loss			2		mJ
E_{off}	Turn-Off Switching Loss			4.3		mJ
C_{ies}	Input Capacitance	$V_{CE} = 25V, f=1MHz,$ $V_{GE} = 0V$		1.79		nF
C_{oes}	Output Capacitance			0.16		nF
C_{res}	Reverse Transfer Capacitance			0.07		nF
I_{SC}	SC Data	$T_P \leq 10\mu s, V_{GE}=15V,$ $T_j=125^\circ C, V_{CC}=360V,$ $V_{CEM} \leq 600V$		270		A
L_{CE}	Stray inductance			30		nH
$R_{CC'+EE'}$	Module lead resistance, terminal to chip	$T_C=25^\circ C$		2.20		m Ω

Electrical Characteristics of DIODE $T_C=25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	$I_F=50A$	$T_j=25^\circ C$	1.3	1.7	V
			$T_j=125^\circ C$		1.4	
Q_r	Diode Reverse Recovered charge	$I_F=50A,$ $V_R=300V,$ $di/dt=-2600A/\mu s,$ $V_{GE}=-15V$	$T_j=25^\circ C$	2.1		μC
			$T_j=125^\circ C$	3.4		
I_{RM}	Diode Peak Reverse Recovery Current		$T_j=25^\circ C$	60		A
			$T_j=125^\circ C$	68		
E_{rec}	Reverse Recovery Energy		$T_j=25^\circ C$	0.42		mJ
			$T_j=125^\circ C$	0.71		

Electrical Characteristics of NTC $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
R ₂₅	Rated resistance			5.0		kΩ
ΔR/R	Deviation of R ₁₀₀	R ₁₀₀ =439Ω	5		5	%
P ₂₅	Power dissipation				20.0	mW
B _{25/50}	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case (IGBT Part, per 1/2 Module)		0.45	°C/W
R _{θJC}	Junction-to-Case (DIODE Part, per 1/2 Module)		0.85	°C/W
R _{θCS}	Case-to-Sink (Conductive grease applied)	0.05		°C/W
Weight	Weight of Module	180		g

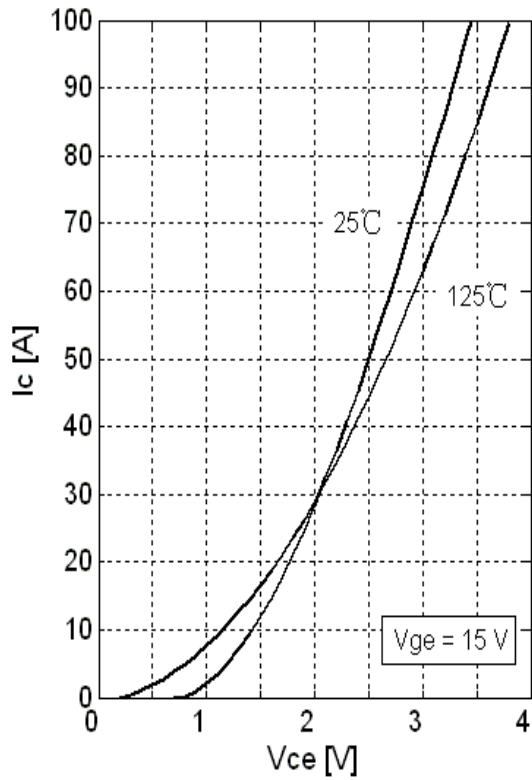


Fig 1. Typical Output Characteristics

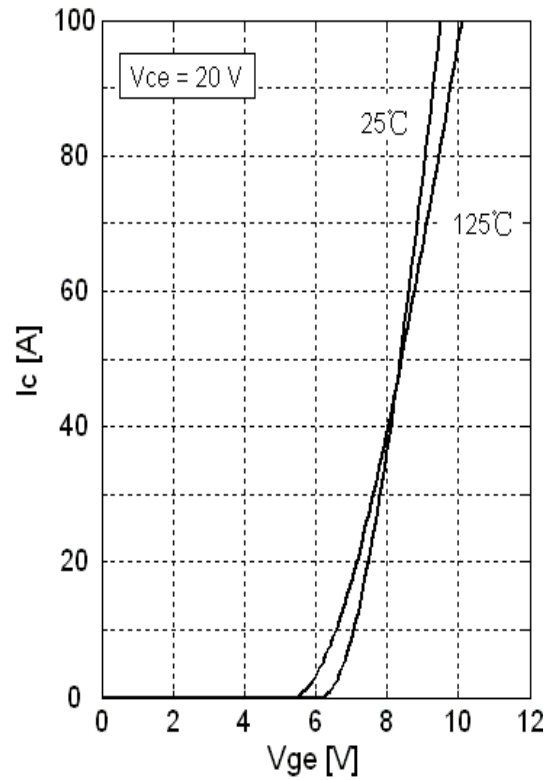


Fig 2. Typical Transfer Characteristics

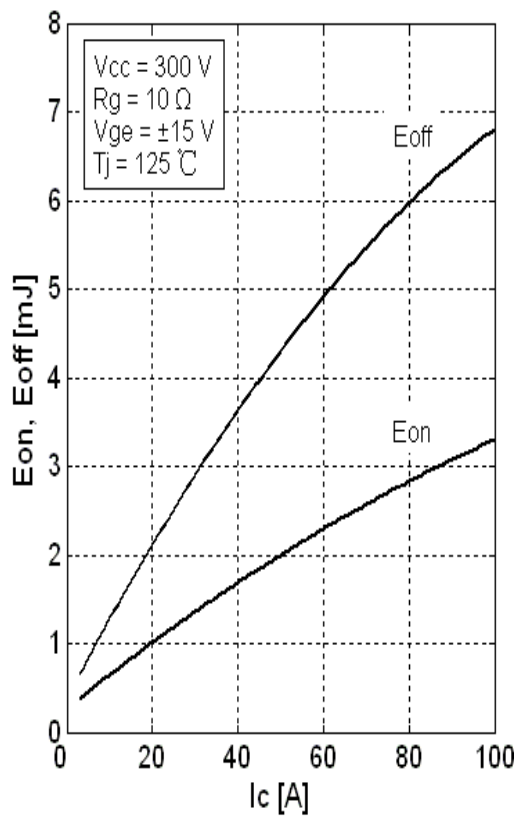


Fig 3. Switching Loss vs. Collector Current

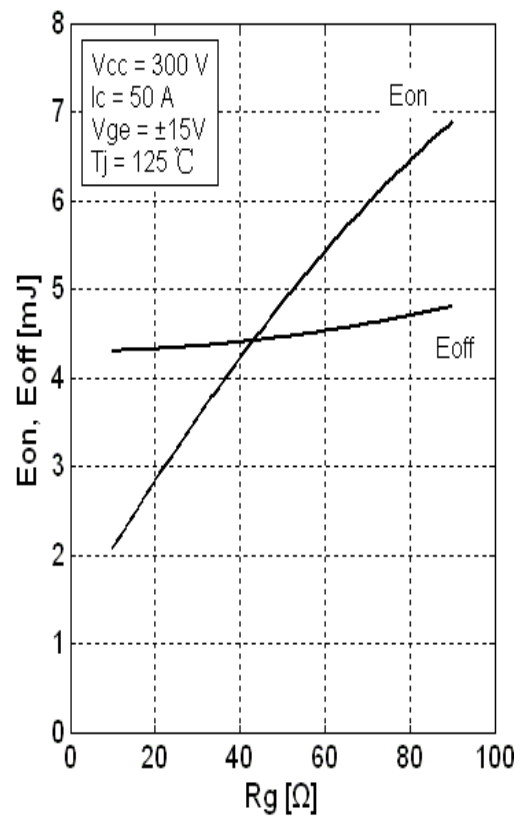


Fig 4. Switching Loss vs. Gate Resistor

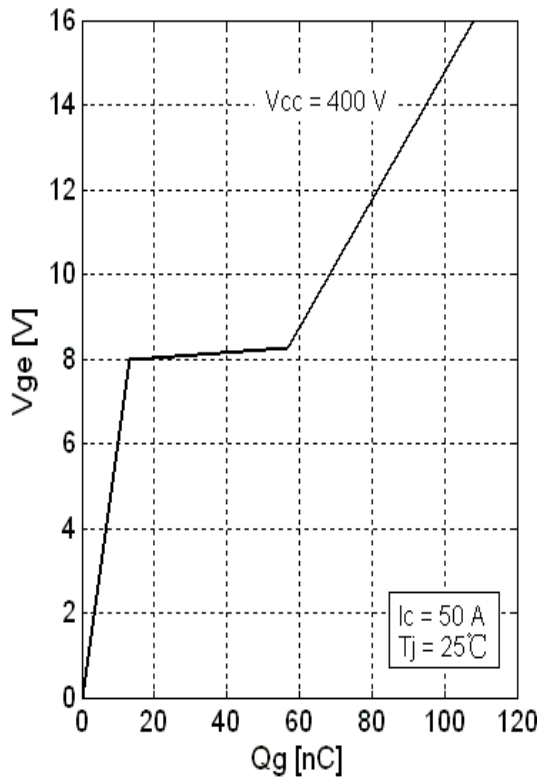


Fig 5. Gate Charge Characteristics.

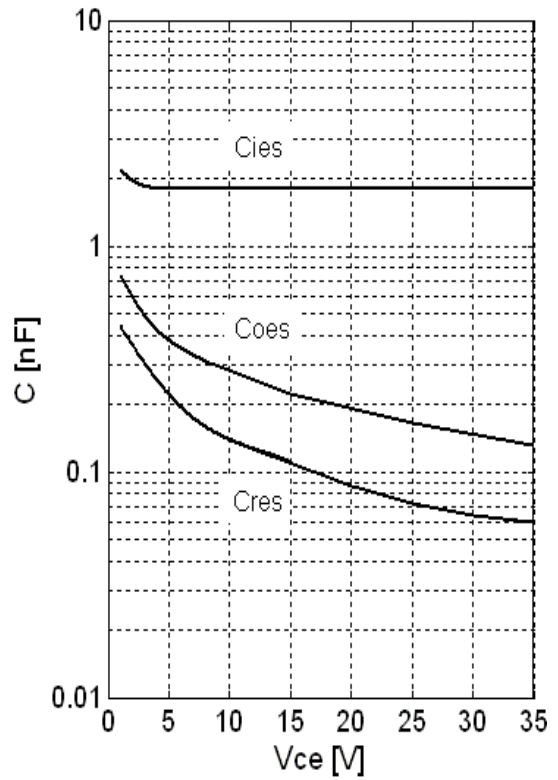


Fig 6. Typical Capacitance vs. Collector-Emitter Voltage

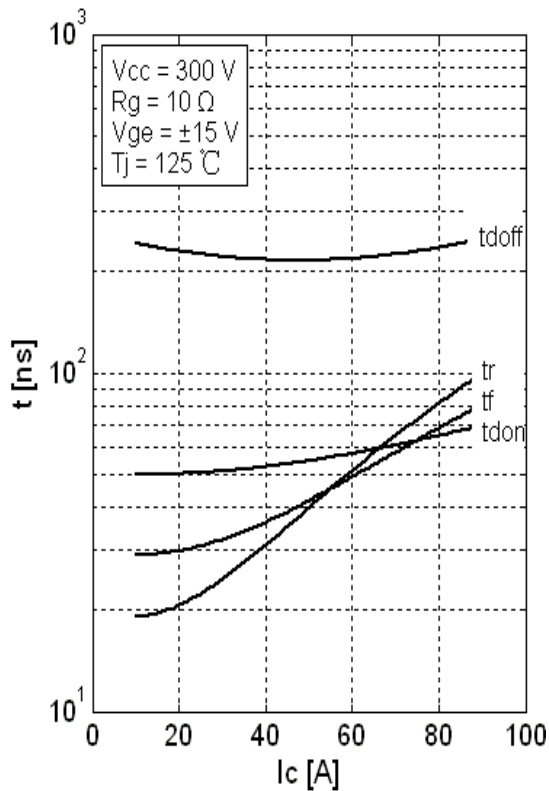


Fig 7. Typical Switching Times vs. I_C

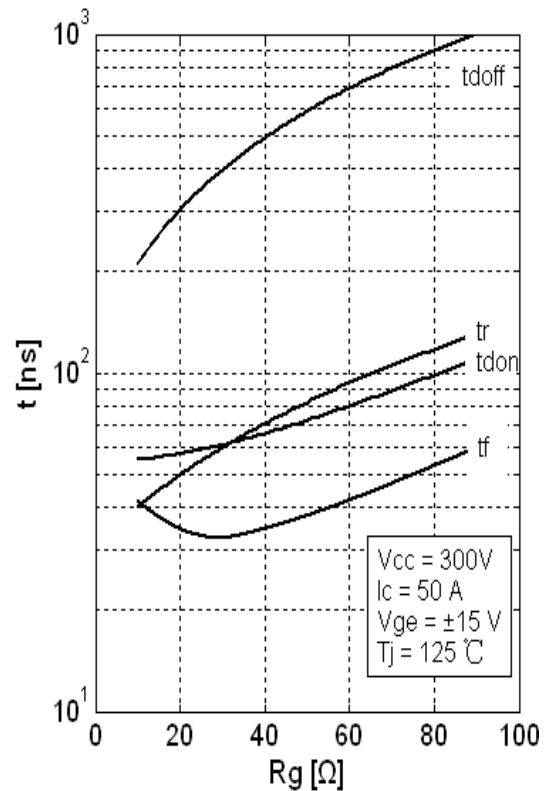


Fig 8. Typical Switching Times vs. Gate Resistance R_G

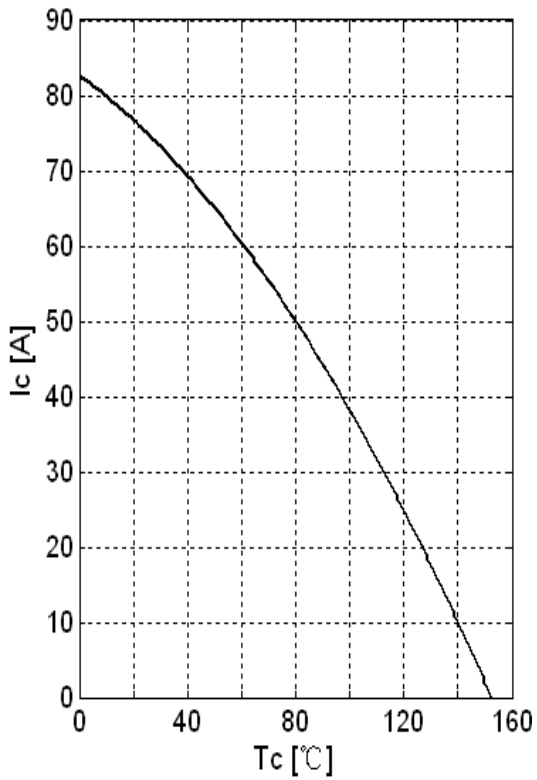


Fig 9. Maximum DC Collector Current vs. Case Temperature

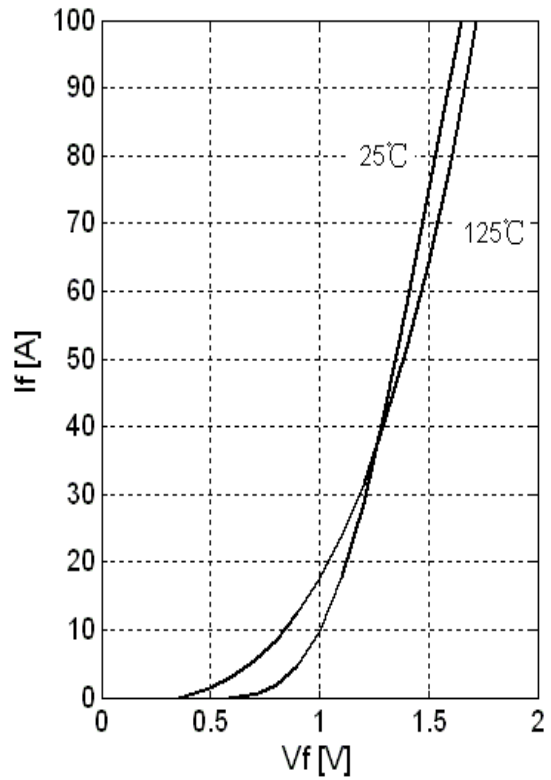


Fig 10. Typical Forward Characteristics (diode)

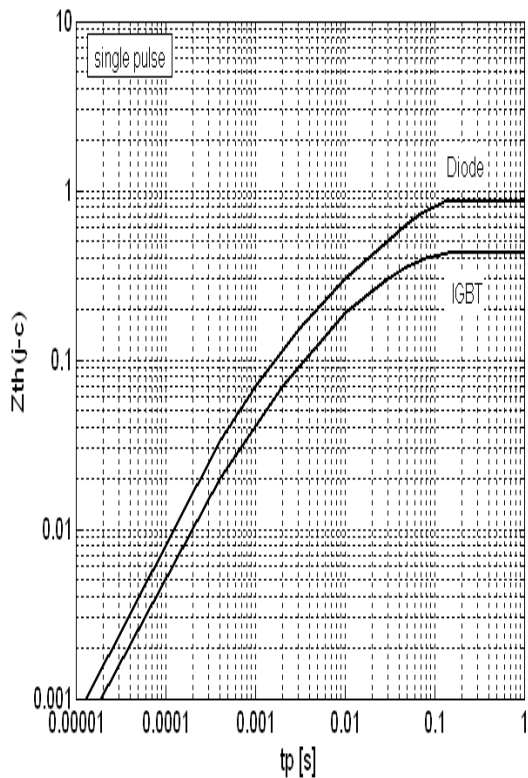


Fig 11. Transient thermal impedance

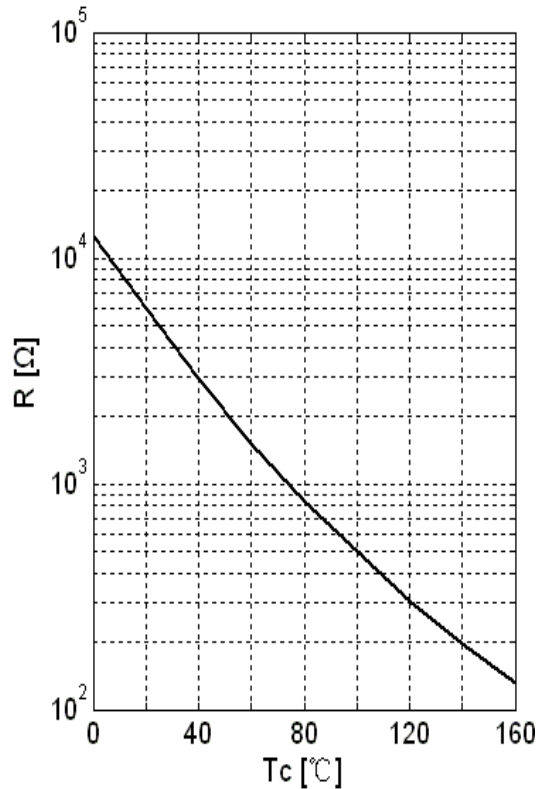
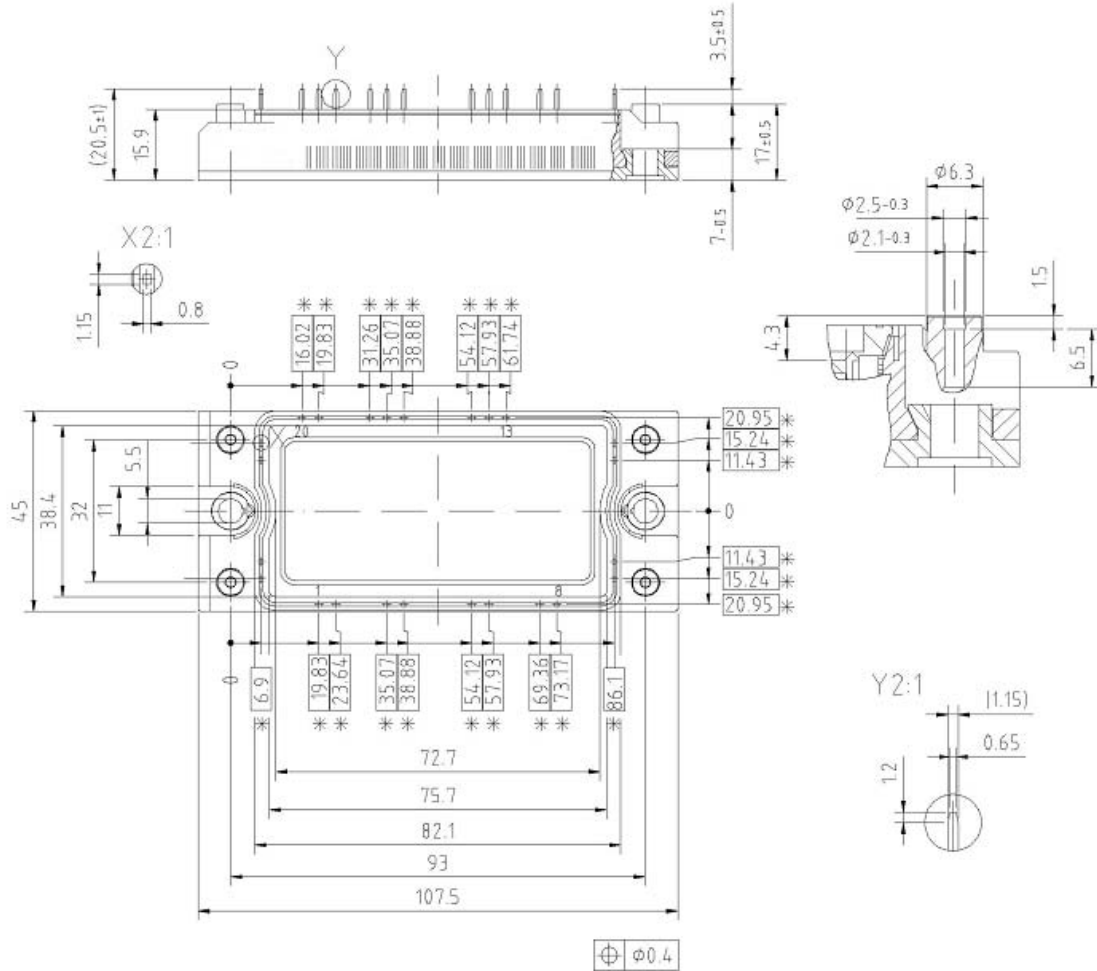


Fig 12. NTC-temperature characteristic

Package Dimension

Dimensions in Millimeters



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